Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN0603-3 (SOT8013) Surface-Mounted Device (SMD) using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Leadless ultra small package 0.63mm x 0.33 mm x 0.25 mm
- Trench MOSFET technology
- Low profile (0.25 mm)
- ElectroStatic Discharge (ESD) protection typically > 1 kV HBM

3. Applications

- · Battery switch
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	0.5	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 0.4 A; T_j = 25 °C		-	800	1100	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source		
3	D	drain	Transparent top view DFN0603-3 (SOT8013)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PMX800ENE		DFN0603-3; plastic, ultra small and leadless full encapsulated package; 3 terminals; 0.225 mm pitch; 0.63 mm x 0.33 mm x 0.25 mm body	SOT8013				

7. Marking

Table 4. Marking codes

Type number	Marking code
PMX800ENE	J

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
drain-source voltage	T _j = 25 °C		-	60	V
gate-source voltage			-20	20	V
drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	0.5	Α
	V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	0.3	Α
peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	1.9	Α
total power dissipation	T _{amb} = 25 °C	[2]	-	300	mW
		[1]	-	500	mW
	T _{sp} = 25 °C		-	4.7	W
junction temperature			-55	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
ode				•	
source current	T _{amb} = 25 °C	[1]	-	0.5	Α
	drain-source voltage gate-source voltage drain current peak drain current total power dissipation junction temperature ambient temperature storage temperature	drain-source voltage	$ \begin{array}{c} drain\text{-source voltage} \\ drain\text{-source voltage} \\ drain current \\ \hline \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ $	$ \begin{array}{c} drain\text{-source voltage} \\ drain\text{-source voltage} \\ drain current \\ \hline \\ V_{GS} = 10 \text{ V}; T_{amb} = 25 ^{\circ}\text{C} \\ \hline \\ V_{GS} = 10 \text{ V}; T_{amb} = 100 ^{\circ}\text{C} \\ \hline \\ peak drain current \\ \hline \\ total power dissipation \\ \hline \\ T_{amb} = 25 ^{\circ}\text{C} \\ \hline \\ T_{amb} = 25 ^{\circ}\text{C} \\ \hline \\ \hline \\ [1] \\ \hline \\ T_{sp} = 25 ^{\circ}\text{C} \\ \hline \\ inction temperature \\ \hline \\ ambient temperature \\ \hline \\ storage temperature \\ \hline \\ \hline \\ ode \\ \hline \\ \hline \\ \hline \\ \hline \\ \\ \hline \\ \\ \hline \\ \\ \\ \\ \hline \\$	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

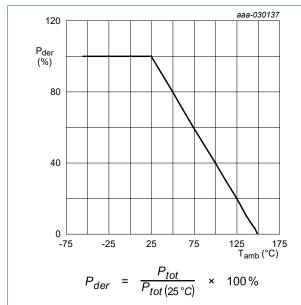


Fig. 1. Normalized total power dissipation as a function of ambient temperature

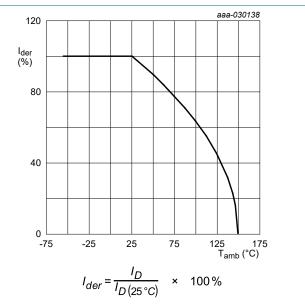


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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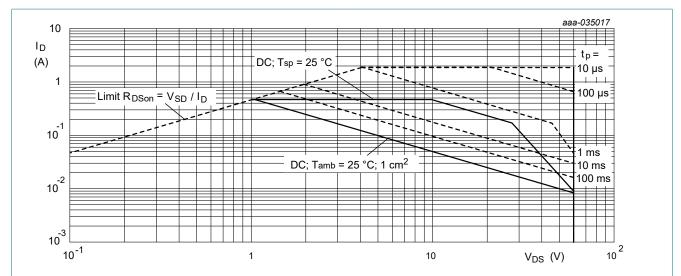


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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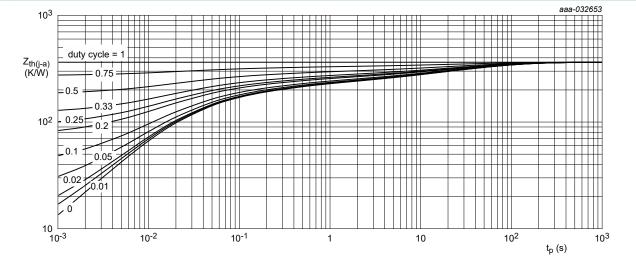
60 V, N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

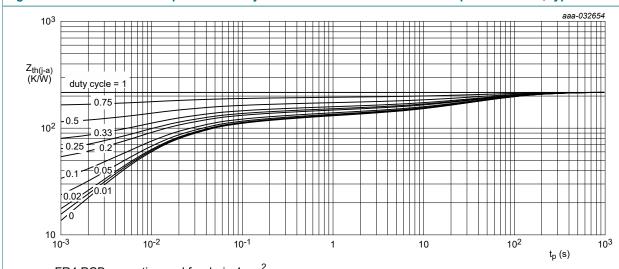
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	360	415	K/W
junction to ambient		[2]	-	215	250	K/W	
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	23	26.5	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.6	2.5	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS} gate leakage current	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
R _{DSon} drain-source on-state resistance	V _{GS} = 10 V; I _D = 0.4 A; T _j = 25 °C	-	800	1100	mΩ	
	resistance	V _{GS} = 10 V; I _D = 0.4 A; T _j = 150 °C	-	1600	2100	mΩ
		V_{GS} = 4.5 V; I_D = 0.3 A; T_j = 25 °C	-	870	1200	mΩ
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 0.4 \text{ A}; T_j = 25 \text{ °C}$	-	1.5	-	S
R_G	gate resistance	f = 1 MHz	-	205	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 0.4 A; V _{GS} = 10 V;	-	0.6	1	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q _{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	32	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	4	-	pF
C _{rss}	reverse transfer capacitance		-	2	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; I _D = 0.4 A; V _{GS} = 10 V;	-	2	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	2	-	ns
t _{d(off)}	turn-off delay time		-	20	-	ns
t _f	fall time		-	9	-	ns
Source-drai	in diode				•	
V_{SD}	source-drain voltage	I _S = 0.48 A; V _{GS} = 0 V; T _j = 25 °C	-	0.8	1.2	V
		-				

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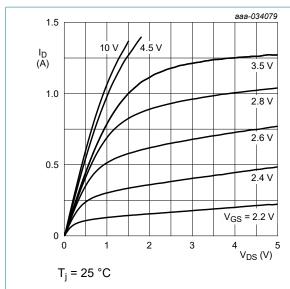


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

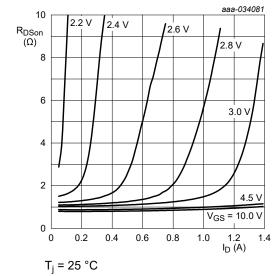


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

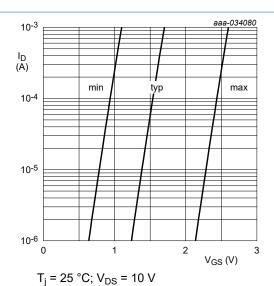


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

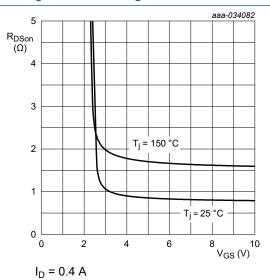


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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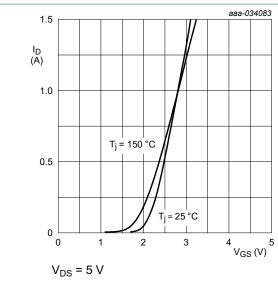


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

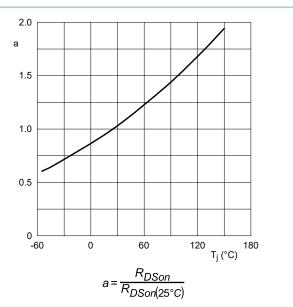


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

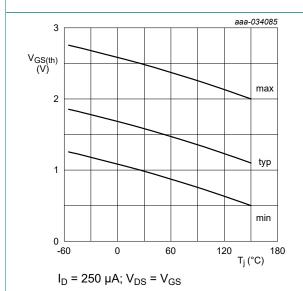


Fig. 12. Gate-source threshold voltage as a function of junction temperature

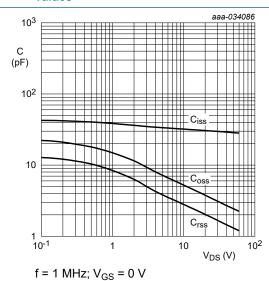


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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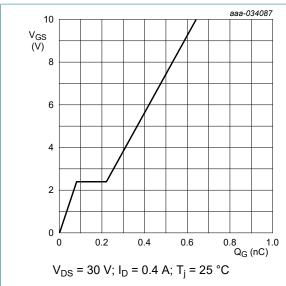


Fig. 14. Gate-source voltage as a function of gate charge; typical values

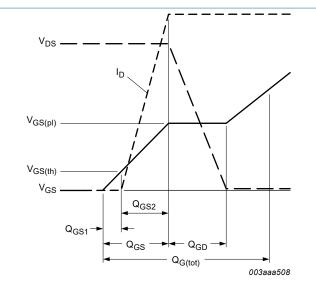


Fig. 15. Gate charge waveform definitions

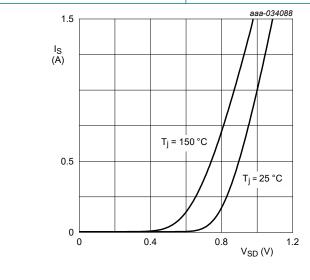
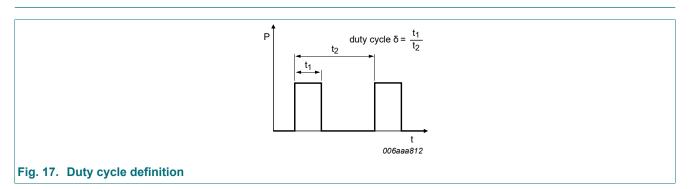


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

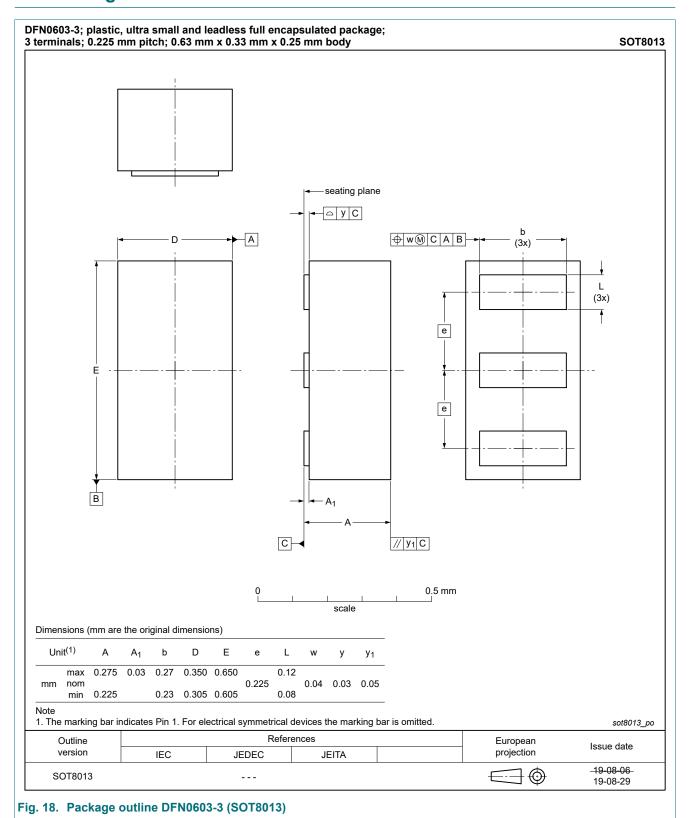
 $V_{GS} = 0 V$



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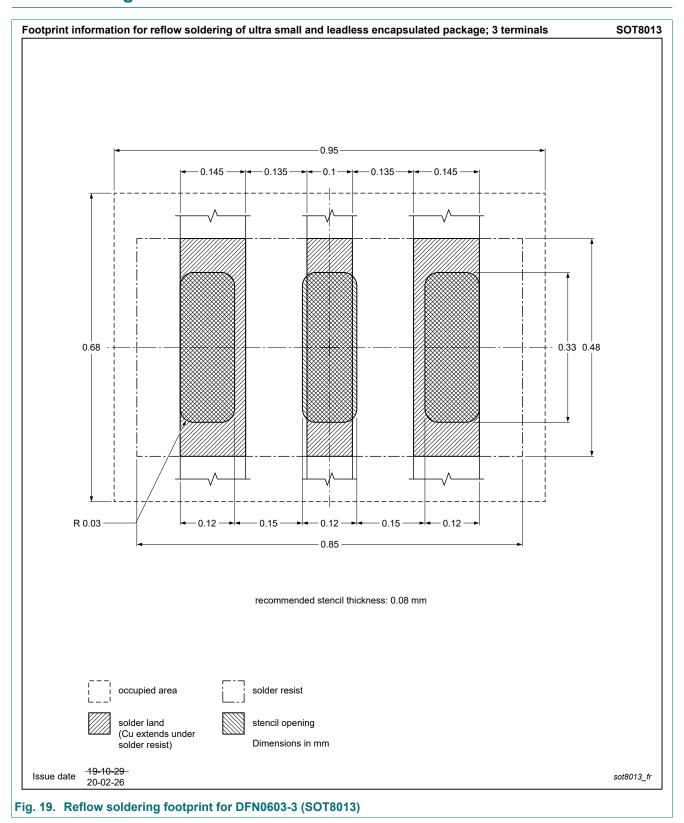
12. Package outline



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13. Soldering



Product data sheet

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14. Revision history

Table 8. Revision history

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Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PMX800ENE v.2	20230712	Product data sheet	-	PMX800ENE v.1				
Modifications:	Changed document	Changed document status to "Product data sheet"						
PMX800ENE v.1	20220609	Preliminary data sheet	-	-				

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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